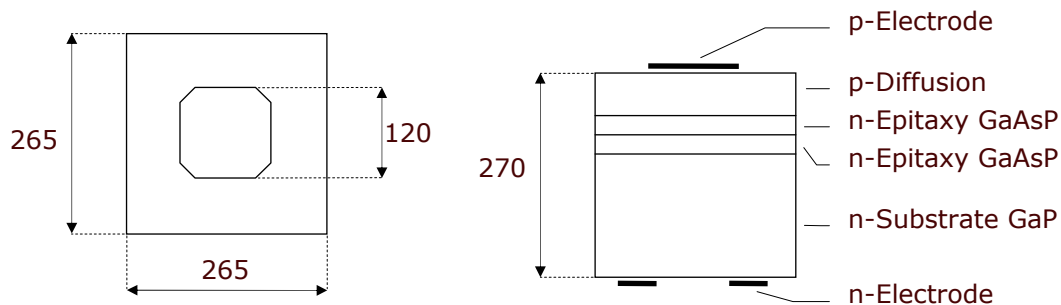


**YELLOW**

**Item No.: 170210**

1. This specification applies to GaAsP / GaP LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contacts can also be circular or square

4. Electrical and optical characteristics (T=25°C)

<i>Parameter</i>	<i>Symbol</i>	<i>Conditions</i>	<i>min</i>	<i>typ</i>	<i>max</i>	<i>Unit</i>
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		2,20	2,50	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 20 \text{ mA}$	2,0	3,0		mcd
dom. wavelength	$\lambda_D$	$I_F = 20 \text{ mA}$		590		nm

\* On request, wafers will be delivered according to luminous intensity classes  
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top  
2) back contact on top

6. Labeling

Type	Lot No.	$I_V$ typ min max	Quantity
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